Taiwan Semiconductor

V_{WM} =5V, 2pF ESD Protection Diode

FEATURES

- Meet IEC61000-4-2(ESD) ±15kV(air) , ±8kV(contact)
- Working Voltage: 5V
- Moisture sensitivity level: level 1, per J-STD-020
- RoHS Compliant
- Halogen-free according to IEC 61249-2-21

KEY PARAMETERS			
PARAMETER	VALUE	UNIT	
P _{PPSM}	100	W	
I _{PP}	3	А	
V _{WM}	5	V	
V _(BR) at I _R = 1 mA	6	V	
V_{C} at I _{PP} = 3 A	15 V		
Package	DFN1006L		
Configuration	Single die		

APPLICATIONS

MECHANICAL DATA

Case: DFN1006L

• Polarity: As marked

• High Speed Data Lines: USB 2.0 / VGA/ DVI /SDI

Molding compound meets UL 94 V-0 flammability rating
Terminal: Matte tin plated leads, solderable per J-STD-002

• Notebooks, Desktops and Servers

• Meet JESD 201 class 1A whisker test

• Weight: 0.742 mg (approximately)

Touch Panel



HALOGEN FREE



PARAMETER	SYMBOL	TESD5V0L1UC	UNIT
Marking code on the device		BH	
Rated random recurring peak Impulse power dissipation (tp=8/20µs waveform)	P _{PPSM}	100	W
Peak impulse current (tp=8/20µs waveform)	I _{PP}	3	А
ESD per IEC 61000-4-2 (Air) ESD per IEC 61000-4-2 (Contact)	V _{ESD}	±15 ±8	kV
Junction temperature range	TJ	-55 to +150	°C
Storage temperature range	T _{STG}	-55 to +150	°C









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ELECTRICAL SPECIFICATIONS (T _A = 25°C unless otherwise noted)						
PARAMETER	CONDITIONS	SYMBOL	MIN	ТҮР	MAX	UNIT
Reverse breakdown voltage (1)	I _R =1 mA	V _(BR)	6	-	9.8	V
Rated working standoff voltage		V _{WM}	-	-	5	V
Reverse current ⁽¹⁾	V _R = 5 V	I _R	-	-	0.1	μA
Clamping voltage (2)	I _{PP} = 1 A	Vc	-	-	10	V
Clamping voltage (2)	I _{PP} = 3 A	Vc	-	-	15	V
Junction capacitance	f = 1 MHz, V _R = 0V	CJ	-	-	2	pF

Notes:

1. Pulse test with PW=30 ms

2. tp=8/20µs waveform

ORDERING INFORMATION			
ORDERING CODE	PACKAGE	PACKING	
TESD5V0L1UC RJG	DFN1006L	5K / 7" Reel	



CHARACTERISTICS CURVES

(T_A = 25°C unless otherwise noted)

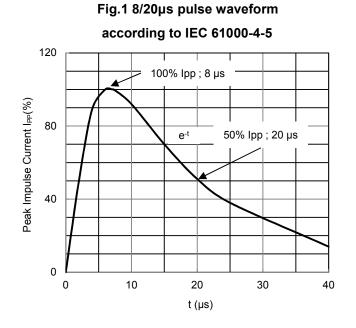


Fig.2 ESD pulse waveform according to IEC 6100-4-2 110 100 90 Peak Impulse Current Ipp(%) 80 70 60 50 40 30 20 10 0 -10 10 30 50 70 t(ns) t_r=0.7ns to 1ns

Fig.3 TLP I-V Curve

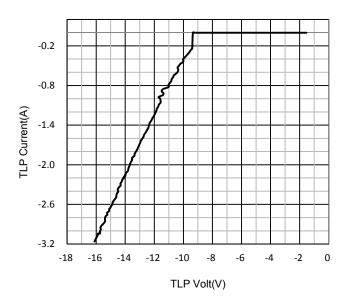
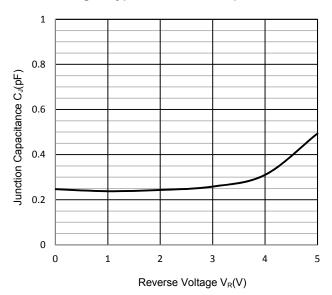


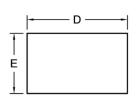
Fig.4 Typical Junction Capacitance



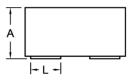


PACKAGE OUTLINE DIMENSION

DFN1006L

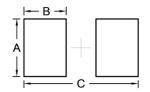






DIM.	Unit (mm)		Unit (inch)		
	Min.	Max.	Min.	Max.	
A	0.46	0.51	0.018	0.020	
b	0.50 (TYP.)		0.020 (TYP.)		
D	0.95	1.05	0.037	0.041	
E	0.55	0.65	0.022	0.026	
L	0.30	(TYP.)	0.012	(TYP.)	

SUGGESTED PAD LAYOUT



Symbol	Unit (mm)	Unit (inch)
A	0.56	0.022
В	0.41	0.016
С	1.11	0.044



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